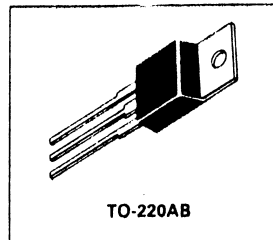


New Jersey Semi-Conductor Products, Inc.

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**2N6342
thru
2N6349**



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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
*Peak Repetitive Off-State Voltage ($T_J = -40$ to $+100^\circ\text{C}$) 1/2 Sine Wave 50 to 60 Hz, Gate Open	V_{ORM}	200 400 600 800	Volts
		2N6342, 2N6346 2N6343, 2N6347 2N6344, 2N6348 2N6345, 2N6349	
*RMS On-State current Full Cycle Sine Wave 50 to 60 Hz	$I_T(\text{RMS})$	8 4	Amps
		$T_C = +80^\circ\text{C}$ $T_C = +90^\circ\text{C}$	
*Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, $T_J = +80^\circ\text{C}$) Preceded and followed by 10 Rated Current	I_{TSM}	100	Amps
Circuit Fusing ($T_J = -40$ to $+100^\circ\text{C}$, $t = 1$ to 8.3 ms)	I^2t	40	A^2s
*Peak Gate Power ($T_C = +80^\circ\text{C}$, Pulse Width = 2 μs)	P_{GM}	20	Watts
*Average Gate Power ($T_C = +80^\circ\text{C}$, $t = 8.3$ ms)	$P_{G(AV)}$	0.5	Watt
*Peak Gate Current	I_{GM}	2	Amps
*Peak Gate Voltage	V_{GM}	10	Volts
*Operating Junction Temperature Range	T_J	-40 to +125	$^\circ\text{C}$
*Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	$^\circ\text{C/W}$

*Indicates JEDEC Registered Data.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, and Either Polarity of MT2 to MT1 Voltage, unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
*Peak Forward or Reverse Blocking Current (Rated V_{DRM} or V_{RRM} , gate open) $T_J = 25^\circ\text{C}$ $T_J = 100^\circ\text{C}$	I_{DRM} , I_{RRM}	—	—	10 2	μA mA
*Peak On-State Voltage ($I_{TM} = 11$ A Peak; Pulse Width = 1 to 2 ms, Duty Cycle $\leq 2\%$)	V_{TM}	—	1.3	1.55	Volts
Gate Trigger Current, Continuous dc ($V_D = 12$ Vdc, $R_L = 100$ Ohms) (Minimum Gate Pulse Width = 2 μs)	I_{GT}				mA
MT2(+), G(+) All Types		—	12	50	
MT2(+), G(-) 2N6346 thru 49		—	12	75	
MT2(-), G(-) All Types		—	20	50	
MT2(-), G(+) 2N6346 thru 49		—	35	75	
*MT2(+), G(+); MT2(-), G(-) $T_C = -40^\circ\text{C}$ All Types		—	—	100	
*MT2(+), G(-); MT2(-), G(+) $T_C = -40^\circ\text{C}$ 2N6346 thru 49, MAC221		—	—	125	
Gate Trigger Voltage, Continuous dc ($V_D = 12$ Vdc, $R_L = 100$ Ohms) (Minimum Gate Pulse Width = 2 μs)	V_{GT}				Volts
MT2(+), G(+) All Types		—	0.9	2	
MT2(+), G(-) 2N6346 thru 49		—	0.9	2.5	
MT2(-), G(-) All Types		—	1.1	2	
MT2(-), G(+) 2N6346 thru 49		—	1.4	2.5	
*MT2(+), G(+); MT2(-), G(-) $T_C = -40^\circ\text{C}$ All Types		—	—	2.5	
*MT2(+), G(-); MT2(-), G(+) $T_C = -40^\circ\text{C}$ 2N6346 thru 49, MAC221		—	—	3	
($V_D = \text{Rated } V_{DRM}$, $R_L = 10$ k Ohms, $T_J = 100^\circ\text{C}$)					
*MT2(+), G(+); MT2(-), G(-) All Types		0.2	—	—	
*MT2(+), G(-); MT2(-), G(+) 2N6346 thru 49, MAC221		0.2	—	—	
*Holding Current ($V_D = 12$ Vdc, Gate Open) ($I_T = 200$ mA)	I_H	—	6	40 75	mA
				$T_C = 25^\circ\text{C}$ $T_C = -40^\circ\text{C}$	
*Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11$ A, $I_{GT} = 120$ mA, Rise Time = 0.1 μs , Pulse Width = 2 μs)	t_{gt}	—	1.5	2	μs
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11$ A, Commutating $di/dt = 4.3$ A/ms, Gate Unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt(c)$	—	5	—	V/ μs